IHSM23R030F1

V_{DSS}	2300 V
$R_{DS(on)}$	30 mΩ

HAWKPACK PF1 series

2300 V, 30 mΩ, Silicon Carbide, Full-bridge Module



Press-fit low-profile

Features

- Complete H-bridge in one module
- Baseplate-less, press-fit pins
- Short commutation loops for fast switching

Typical applications

- Two-level converters on 1500 V DC buses
- 1500 V DC solar inverters and battery storage
- High-power DC-DC converters

Description

2300 V, 30 mΩ silicon-carbide MOSFET full-bridge module in a 62.8 × 33.8 mm baseplate-less housing.

Key specifications

Parameter	Value
V_{DSS}	2300 V
$R_{DS(on)}$ typ., T_{vj} = 25 °C	30 mΩ
I_D nominal	50 A
Topology	Full-bridge
T_{vj} op. max	175 °C
Outline	62.8 × 33.8 mm, baseplate-less, press-fit pins

Full characterization data

Thermal resistance, switching energies and times, capacitances, gate charge and typical characteristic curves for IHSM23R030F1 are available on request: request the full data or write to sales@ironhawksemi.com.

Package

Press-fit low-profile. Mechanical outline drawing, STEP model and PCB footprint available on request.

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Ordering information

Part number	Packing	MOQ	Lead time
IHSM23R030F1	Box	On request	On request

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